

# N-channel 30 V 2.7 mΩ logic level MOSFET in TO-220Rev. 02 — 2 November 2010Product of the sector of the

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- 1.3 Applications
  - DC-to-DC converters
  - Load switching

- Suitable for logic level gate drive sources
- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data	ference data
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	[2]	-	2.2	2.7	mΩ
Dynamic o	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A;		-	8	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	32	-	nC
Avalanche	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^{\circ}C; \\ I_{D} = 100 \text{ A}; \ V_{sup} \leq 30 \text{ V}; \\ R_{GS} = 50 \ \Omega; \ unclamped \end{array} $		-	-	300	mJ

[1] Continuous current is limited by package.

[2] Measured 3 mm from package.

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#### N-channel 30 V 2.7 m $\Omega$ logic level MOSFET in TO-220

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R7-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

N-channel 30 V 2.7 mΩ logic level MOSFET in TO-220

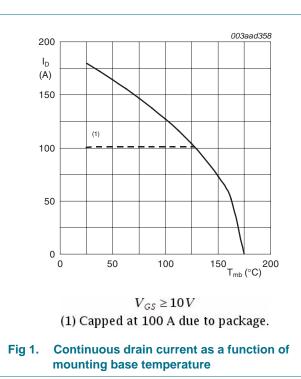
### 4. Limiting values

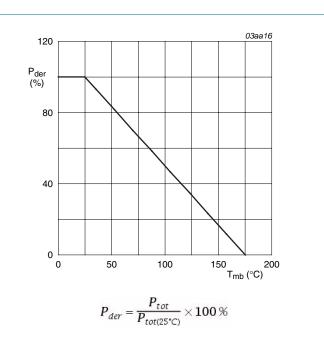
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	30	V
gate-source voltage			-20	20	V
drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	[1]	-	100	А
	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	100	А
peak drain current	pulsed; $t_p \le 10 \ \mu$ s; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	730	А
total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	170	W
storage temperature			-55	175	°C
junction temperature			-55	175	°C
diode					
source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	730	А
gedness					
non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	300	mJ
	drain-source voltage drain-gate voltage gate-source voltage drain current beak drain current total power dissipation storage temperature junction temperature diode source current peak source current peak source current peak source current non-repetitive drain-source	$\begin{array}{ll} \mbox{drain-source voltage} & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C} \\ \mbox{drain-gate voltage} & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C}; \ R_{GS} = 20 \ k\Omega \\ \mbox{gate-source voltage} \\ \mbox{drain current} & \frac{V_{GS} = 10 \ V; \ T_{mb} = 100 \ {}^\circ\mbox{C}; \ see \ Figure 1}{V_{GS} = 10 \ V; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 1} \\ \mbox{peak drain current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 3} \\ \mbox{total power dissipation} & T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 2} \\ \mbox{storage temperature} \\ \mbox{junction temperature} \\ \mbox{diode} \\ \mbox{source current} & T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & pulsed; \ t_p \le 10 \ V; \ T_{j(init)} = 25 \ {}^\circ\mbox{C}; \ t_p = 100 \ A; \\ \end{tabular}$	$\begin{array}{ll} \mbox{drain-source voltage} & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C} \\ \mbox{drain-gate voltage} & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C}; \ R_{GS} = 20 \ k\Omega \\ \mbox{gate-source voltage} & & & & & & & & & & & & & & & & & & &$	$\begin{array}{cccc} drain-source voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C} & - & \\ drain-gate voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega & - & \\ gate-source voltage & -20 & \\ drain current & V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ \text{see Figure 1} & [1] & - & \\ \hline V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 1} & [1] & - & \\ \hline v_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 3} & - & \\ total power dissipation & T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 2} & - & \\ \text{storage temperature} & -55 & \\ junction temperature & -55 & \\ \textbf{diode} & & \\ \text{source current} & T_{mb} = 25 \ ^{\circ}\text{C} & & \ \ 11 & - & \\ pulsed; \ t_p \leq 10 \ \text{\mu}\text{s}; \ T_{mb} = 25 \ ^{\circ}\text{C} & & \ \ 11 & - & \\ peak \ \text{source current} & T_{mb} = 25 \ ^{\circ}\text{C} & & \ \ 11 & - & \\ pulsed; \ t_p \leq 10 \ \text{\mu}\text{s}; \ T_{mb} = 25 \ ^{\circ}\text{C} & & \ \ 11 & - & \\ peak \ \text{source current} & V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C} & & - & \\ \hline \textbf{gedness} & & \\ \text{non-repetitive drain-source} & V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_D = 100 \ \text{A}; & - & \\ \end{array}$	$\begin{array}{cccccccc} drain-source \ voltage & T_{j} \geq 25\ ^{\circ}C;\ T_{j} \leq 175\ ^{\circ}C & - & 30 \\ drain-gate \ voltage & T_{j} \geq 25\ ^{\circ}C;\ T_{j} \leq 175\ ^{\circ}C;\ R_{GS} = 20\ k\Omega & - & 30 \\ gate-source \ voltage & -20 & 20 \\ drain \ current & V_{GS} = 10\ V;\ T_{mb} = 100\ ^{\circ}C;\ see\ Figure\ 1 & 11 & - & 100 \\ \hline V_{GS} = 10\ V;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 1 & 11 & - & 100 \\ \hline v_{GS} = 10\ V;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 1 & 11 & - & 100 \\ \hline peak\ drain\ current & pulsed;\ t_{p} \leq 10\ \mu s;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 3 & - & 730 \\ total\ power\ dissipation & T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 2 & - & 170 \\ storage\ temperature & -55 & 175 \\ junction\ temperature & -55 & 175 \\ diode & & & \\ source\ current & T_{mb} = 25\ ^{\circ}C & 10\ \mu s;\ T_{mb} = 25\ ^{\circ}C & - & 730 \\ peak\ source\ current & T_{mb} = 25\ ^{\circ}C & 10\ \mu s;\ T_{mb} = 25\ ^{\circ}C & - & 730 \\ peak\ source\ current & V_{GS} = 10\ \mu s;\ T_{mb} = 25\ ^{\circ}C;\ I_{D} = 100\ A; & - & 300 \\ \end{array}$

[1] Continuous current is limited by package.

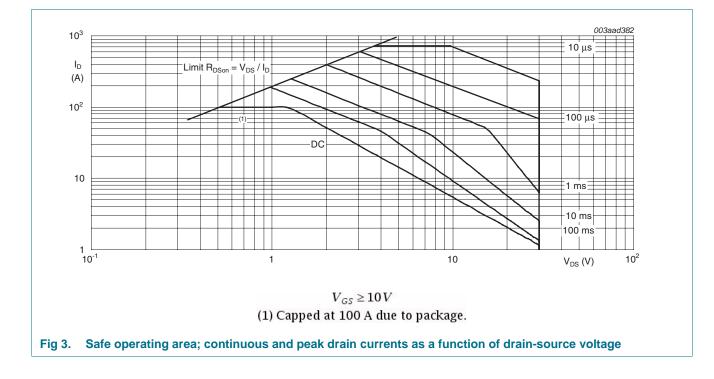






## PSMN2R7-30PL

#### N-channel 30 V 2.7 m $\Omega$ logic level MOSFET in TO-220



10<sup>-4</sup>

Fig 4.

10<sup>-6</sup>

values

10-5

10-4

tp

Т

10<sup>-1</sup>

10<sup>-2</sup>

т

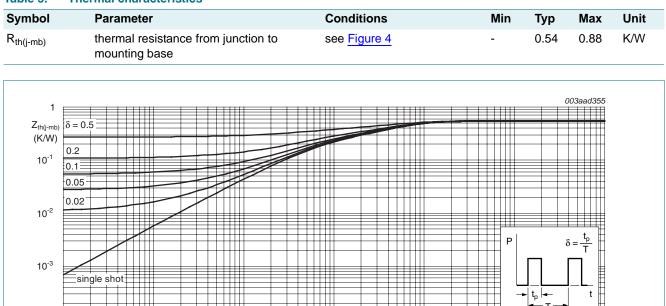
t<sub>p</sub> (s)

t

1

N-channel 30 V 2.7 mΩ logic level MOSFET in TO-220

#### **Thermal characteristics** 5.



10<sup>-3</sup>

Transient thermal impedance from junction to mounting base as a function of pulse duration; typical

#### Table 5. **Thermal characteristics**

N-channel 30 V 2.7 m $\Omega$  logic level MOSFET in TO-220

### 6. Characteristics

#### Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	5	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS} = -16 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \; V; \; I_{D} = 15 \; A; \; T_{j} = 25 \; ^{\circ}C; \\ \text{see} \; \underline{Figure 12} \end{array}$	-	2.7	3.6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 13</u>	-	-	5.13	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 13</u>	-	-	6.84	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 100 °C; see <u>Figure 13</u>	-	-	3.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; see <u>Figure 12</u>	<u>[1]</u> -	2.2	2.7	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	66	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	60	-	nC
		$I_D = 25 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};$	-	32	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	12	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	6.4	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	5.6	-	nC
Q <sub>GD</sub>	gate-drain charge		-	8	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 15 V	-	2.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 12 V; $V_{GS}$ = 0 V; f = 1 MHz;	-	3954	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	822	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	356	-	pF

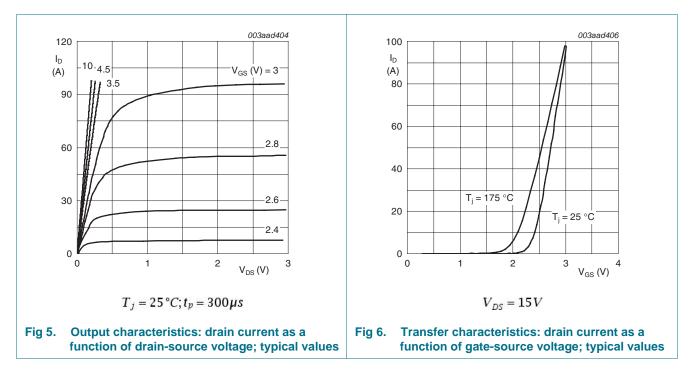
#### N-channel 30 V 2.7 m $\Omega$ logic level MOSFET in TO-220

#### Table 6. Characteristics ...continued

Tested to JEDEC standards where applicable.

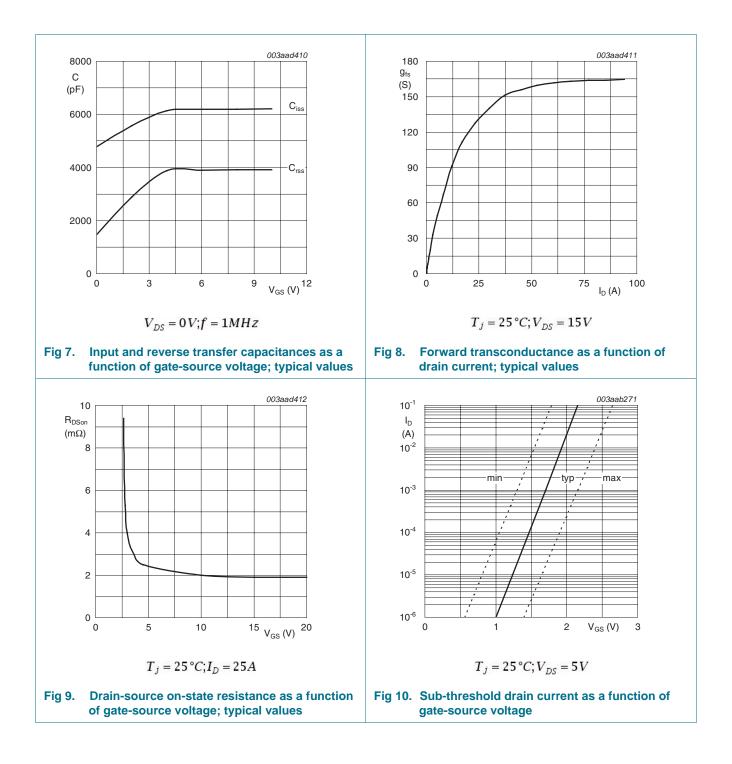
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d(on)</sub>	turn-on delay time	$\label{eq:VDS} \begin{split} V_{DS} = 12 \; V; \; R_L = 0.5 \; \Omega; \; V_{GS} = 4.5 \; V; \\ R_{G(ext)} = 4.7 \; \Omega \end{split}$	-	46	-	ns
t <sub>r</sub>	rise time		-	82	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	74	-	ns
t <sub>f</sub>	fall time		-	35	-	ns
Source-dra	in diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	40	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 V; V_{DS} = 12 V$	-	33	-	nC

[1] Measured 3 mm from package.



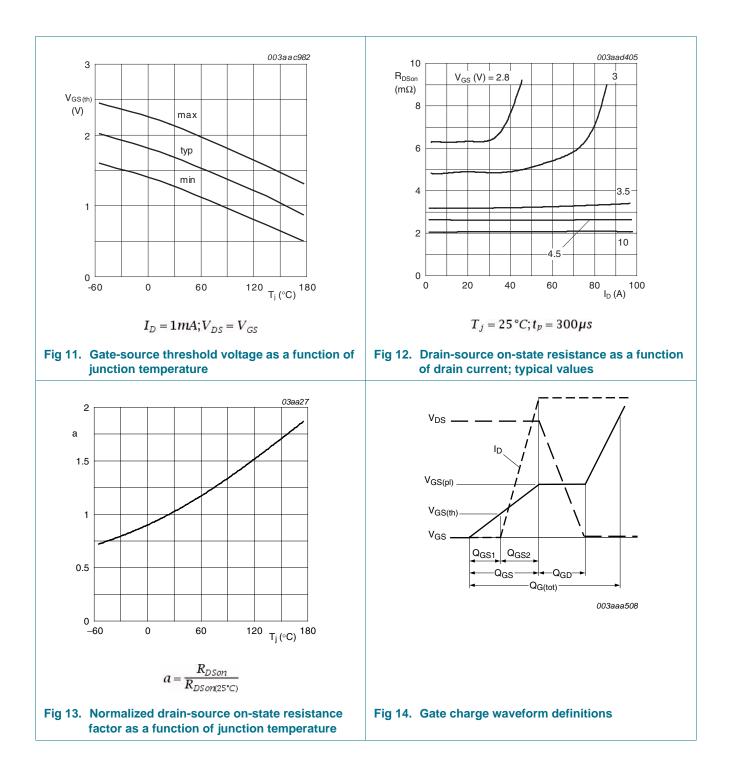
# PSMN2R7-30PL

#### N-channel 30 V 2.7 m $\Omega$ logic level MOSFET in TO-220



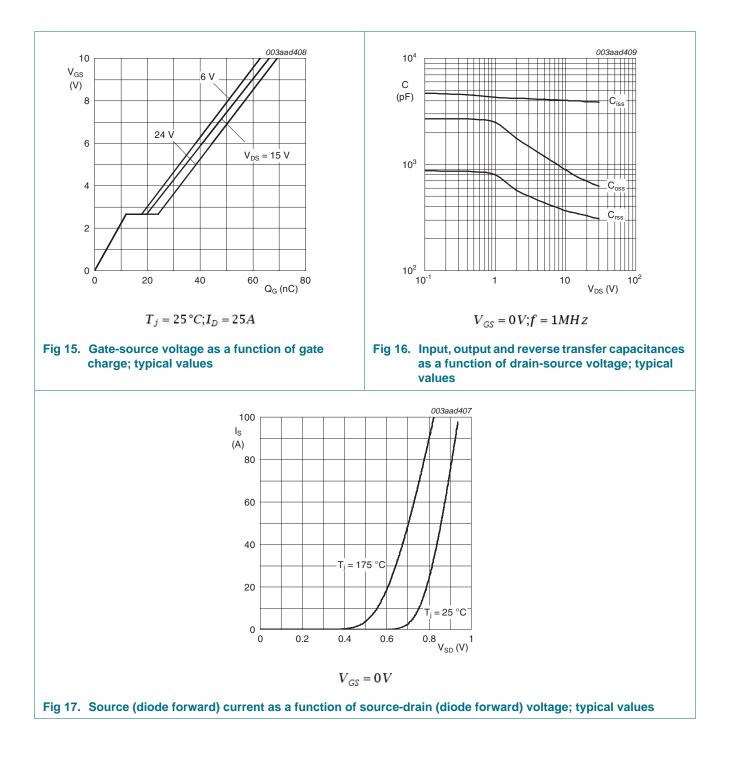
# PSMN2R7-30PL

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# PSMN2R7-30PL

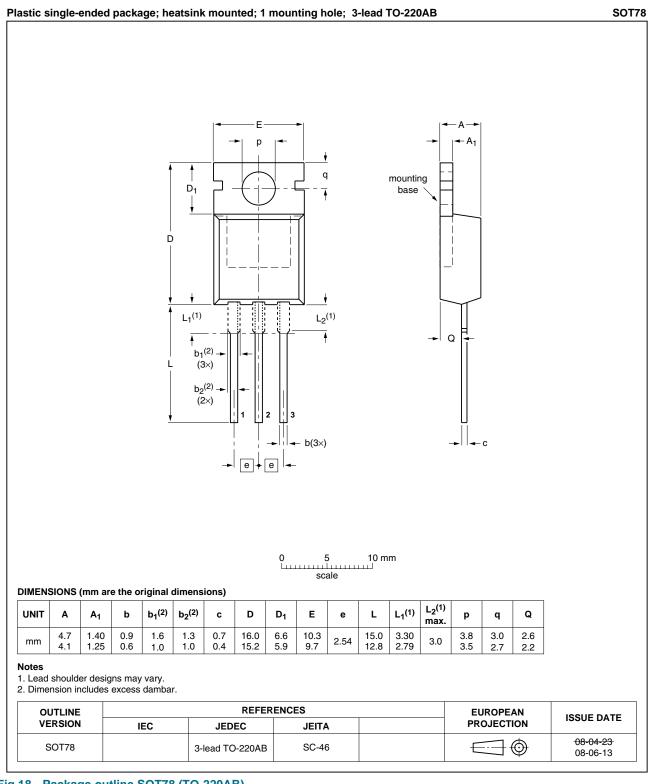
#### N-channel 30 V 2.7 m $\Omega$ logic level MOSFET in TO-220



PSMN2R7-30PL

#### N-channel 30 V 2.7 m $\Omega$ logic level MOSFET in TO-220

### 7. Package outline



#### Fig 18. Package outline SOT78 (TO-220AB)

PSMN2R7-30PL
Product data sheet

#### N-channel 30 V 2.7 mΩ logic level MOSFET in TO-220

### 8. Revision history

Table 7. Revision I	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R7-30PL v.2	20101102	Product data sheet	-	PSMN2R7-30PL v.1
Modifications:	<ul> <li>Status change</li> </ul>	d from objective to product.		
	<ul> <li>Various chang</li> </ul>	es to content.		
PSMN2R7-30PL v.1	20100226	Objective data sheet	-	-

N-channel 30 V 2.7 mΩ logic level MOSFET in TO-220

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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